



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Diodes

BAV199DW Multi-Chip DIODES

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 200 mA

Collector-base voltage

V_R : 85 V

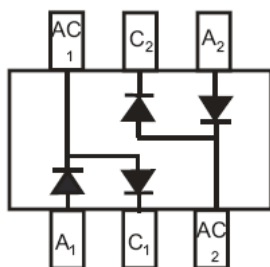
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-363



MARKING:K52



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	85			V
Reverse voltage leakage current	I_R	$V_R=75V$			5	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$			0.9 1.0 1.1 1.25	V
Junction capacitance	C_j	$V_R=0V$ $f=1MHz$		2		pF
Reveres recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$ $R_L=100\Omega$			3	nS

Typical Characteristics

BAV199DW

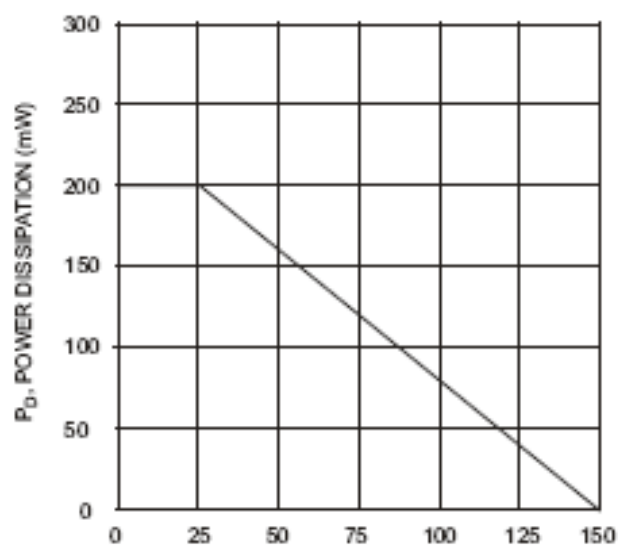


Fig. 1 Power Derating Curve

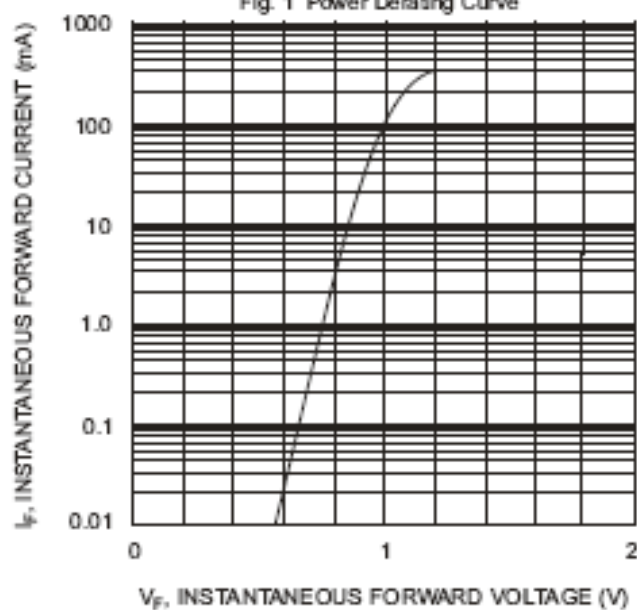


Fig. 3 Typical Forward Characteristics

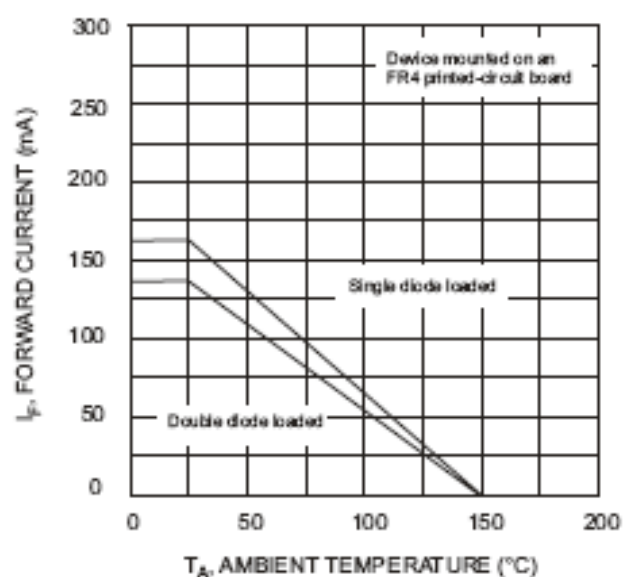


Fig. 2 Current Derating Curve

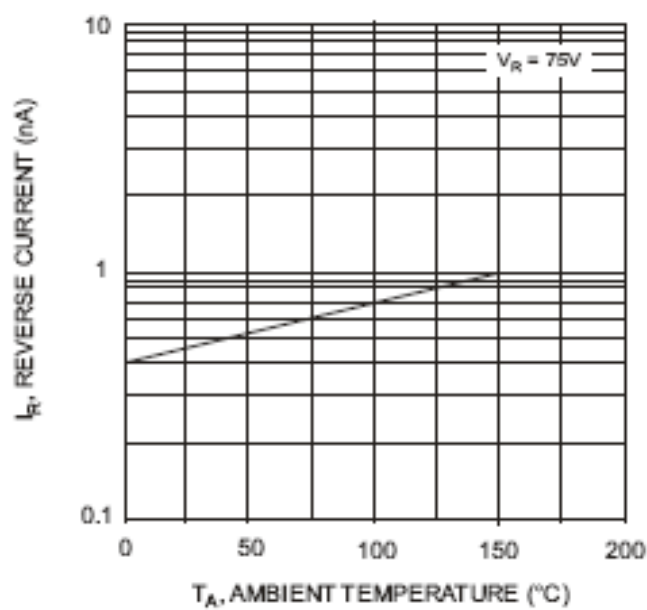


Fig. 4 Typical Reverse Characteristics